Infineon technologies

Preliminary data

SDP10S30, SDB10S30 SDT10S30

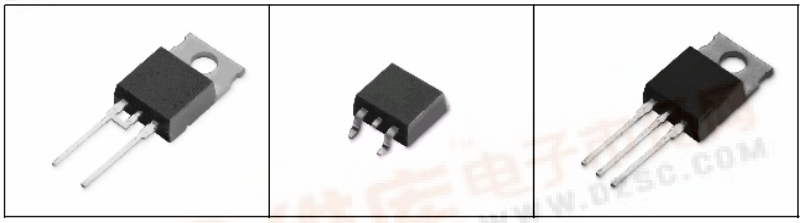
Silicon Carbide Schottky Diode

- Revolutionary semiconductor material - Silicon Carbide
- Switching behavior benchmark
- No reverse recovery
- No temperature influence on the switching behavior
- No forward recovery

Product Summary

V_{RRM}	300	V
Q_c	23	nC
I_F	10	A

P-TO220-2-2. P-TO220-3.SMD P-TO220-3-1.



Type	Package	Ordering Code	Marking	Pin 1	PIN 2	PIN 3
SDP10S30	P-TO220-3-1.	Q67040-S4372	D10S30	n.c.	C	A
SDB10S30	P-TO220-3.SMD	Q67040-S4373	D10S30	n.c.	C	A
SDT10S30	P-TO220-2-2.	Q67040-S4447	D10S30	C	A	

Maximum Ratings,at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous forward current, T_C=100°C	I_F	10	A
RMS forward current, f=50Hz	I_{FRMS}	14	
Surge non repetitive forward current, sine halfwave T_C=25°C, t_p=10ms	I_{FSM}	36	
Repetitive peak forward current T_j=150°C, T_C=100°C, D=0.1	I_{FRM}	45	
Non repetitive peak forward current t_p=10µs, T_C=25°C	I_{FMAX}	100	
i^2t value, T_C=25°C, t_p=10ms	$\int i^2dt$	6.5	A²s
Repetitive peak reverse voltage	V_{RRM}	300	V
Surge peak reverse voltage	V_{RSM}	300	
Power dissipation, T_C=25°C	P_{tot}	65	W
Operating and storage temperature	T_j , T_{stg}	-55... +175	°C

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - case	R_{thJC}	-	-	2.3	K/W
SMD version, device on PCB:	R_{thJA}				
P-TO263-3-2: @ min. footprint		-	-	62	
P-TO263-3-2: @ 6 cm^2 cooling area [1)]		-	35	-	

Electrical Characteristics, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Diode forward voltage	V_F				V
I_F=10A, T_j=25°C		-	1.5	1.7	
I_F=10A, T_j=150°C		-	1.5	1.9	
Reverse current	I_R				µA
V_R=300V, T_j=25°C		-	15	200	
V_R=300V, T_j=150°C		-	20	1000	

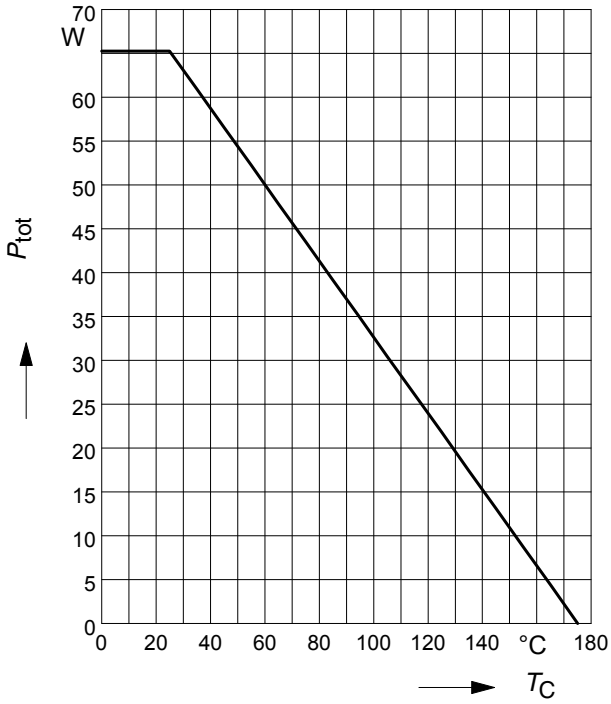
[1]Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical without blown air.

Electrical Characteristics,at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics					
Total capacitive charge[1)]	Q_c	-	23	-	nC
V_R=200V, I_F=10A, di_F/dt=-200A/µs, T_j=150°C					
Switching time[2)]	t_{rr}	-	n.a.	-	ns
V_R=200V, I_F=10A, di_F/dt=-200A/µs, T_j=150°C					
Total capacitance	C				pF
V_R=0V, T_C=25°C, f=1MHz		-	600	-	
V_R=150V, T_C=25°C, f=1MHz		-	55	-	
V_R=300V, T_C=25°C, f=1MHz		-	40	-	

1 Power dissipation

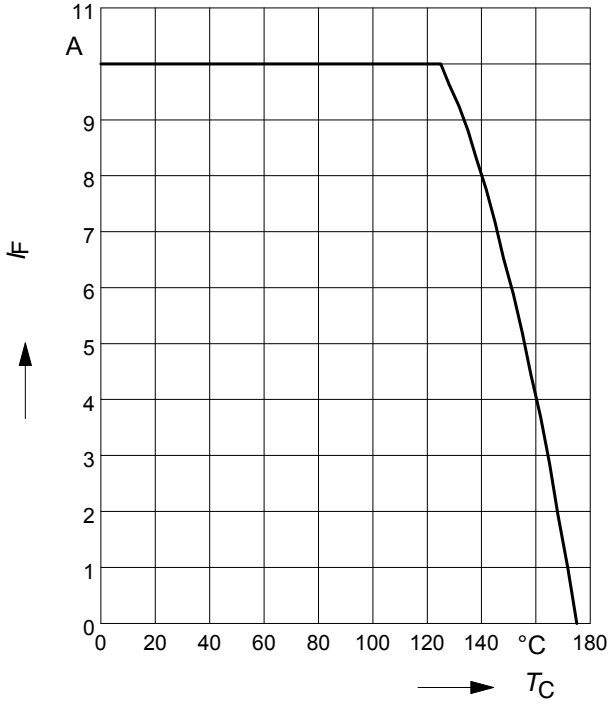
$P_{tot} = f(T_C)$



2 Diode forward current

$I_F = f(T_C)$

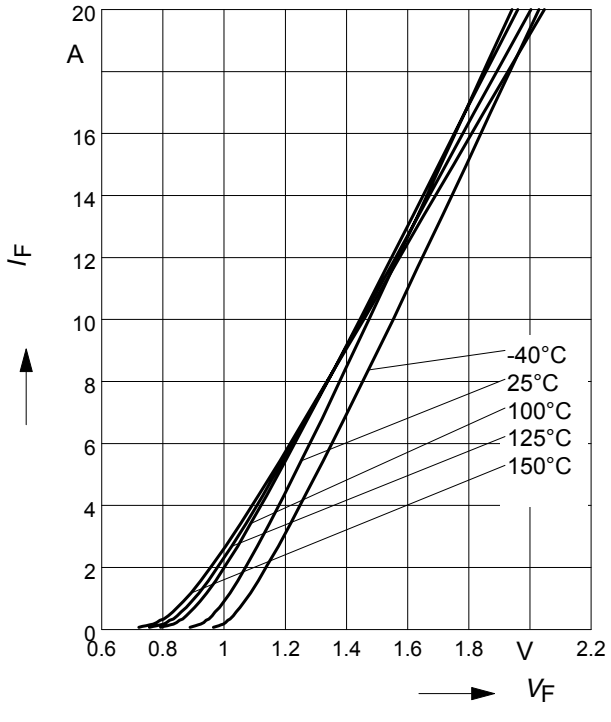
parameter: $T_j \leq 175$ °C



3 Typ. forward characteristic

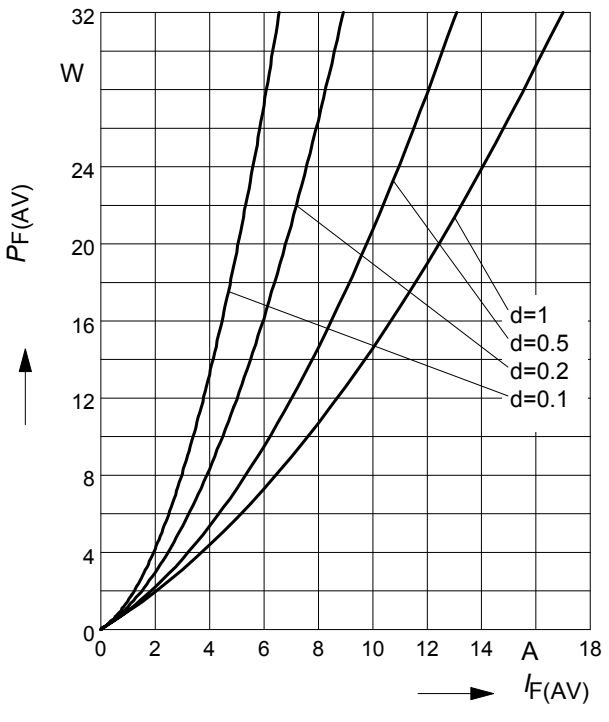
$I_F = f(V_F)$

parameter: T_j , tp = 350 µs



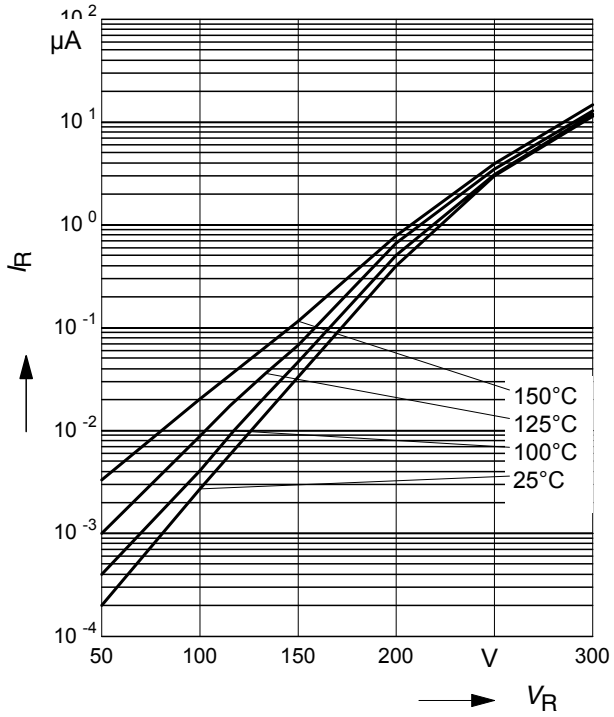
4 Typ. forward power dissipation vs. average forward current

$P_{F(AV)}=f(I_F)$ T_C=100°C, $d = t_p/T$



5 Typ. reverse current vs. reverse voltage

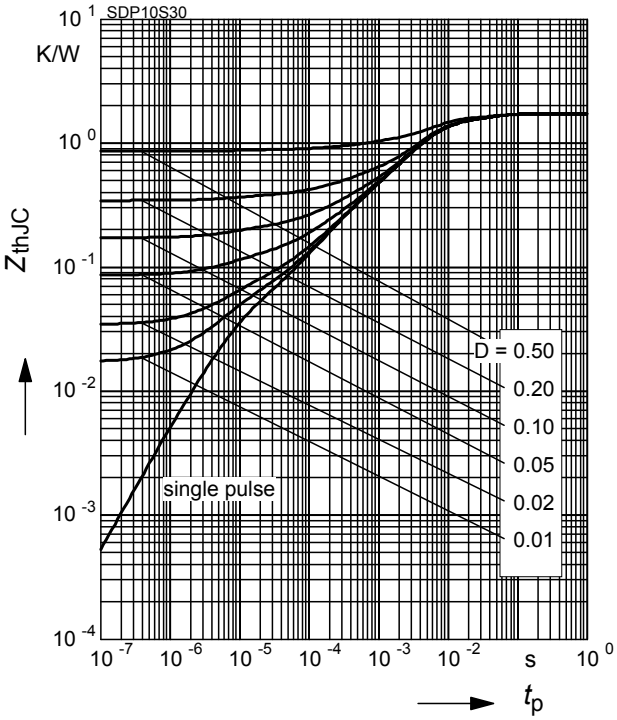
$I_R=f(V_R)$



6 Transient thermal impedance

$Z_{thJC} = f(t_p)$

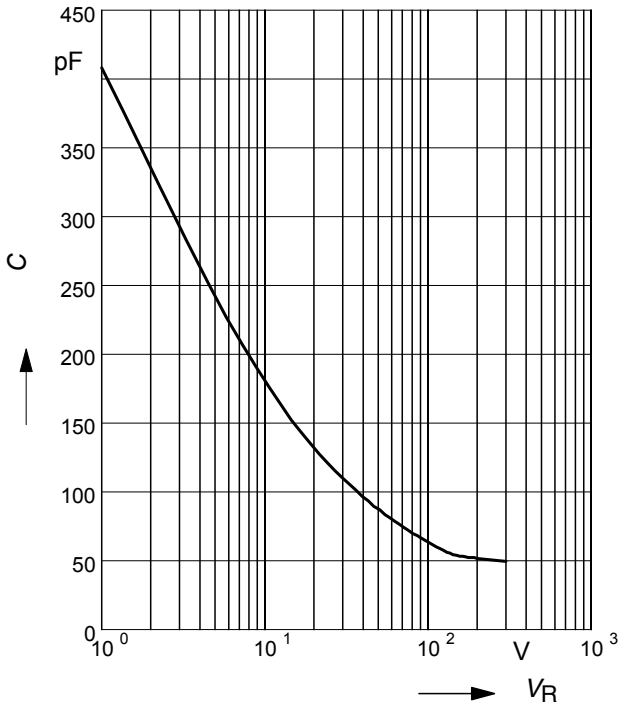
parameter : $D = t_p/T$



7 Typ. capacitance vs. reverse voltage

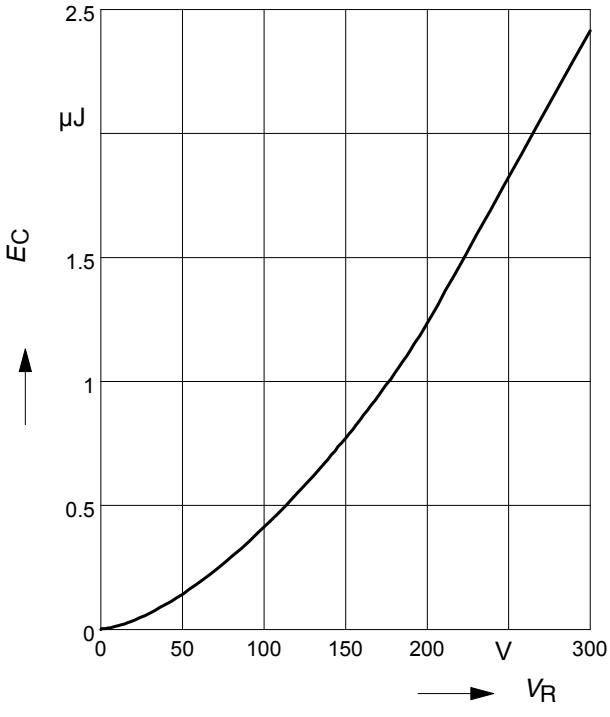
$C= f(V_R)$

parameter: T_C = 25 °C, f = 1 MHz



8 Typ. *C* stored energy

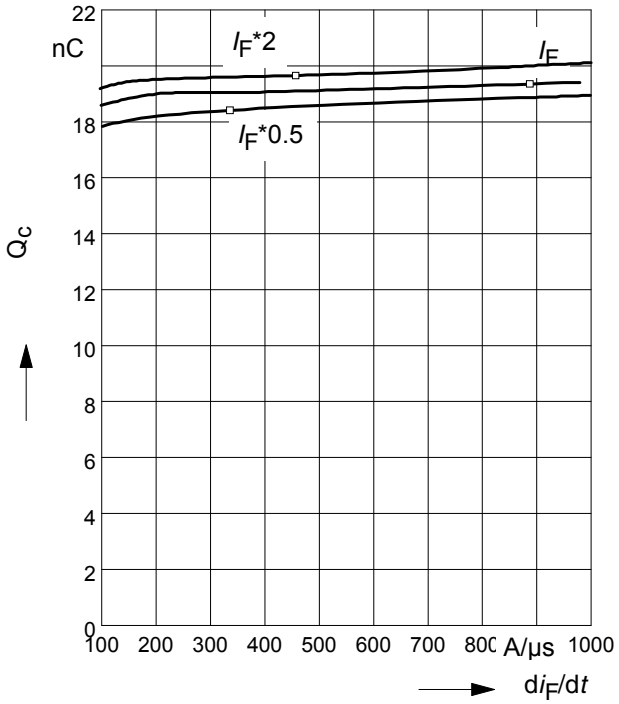
$E_C=f(V_R)$



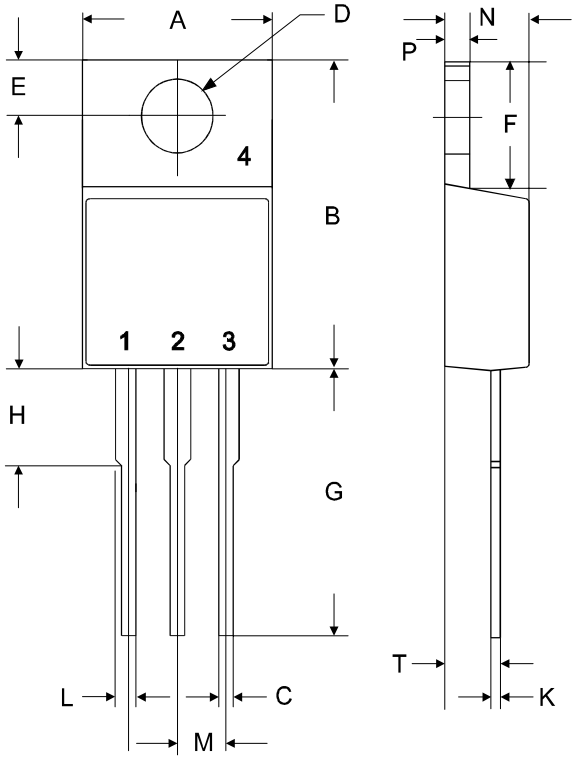
9 Typ. capacitive charge vs. current slope

$Q_c = f(di_F/dt)$

parameter: T_j = 150 °C

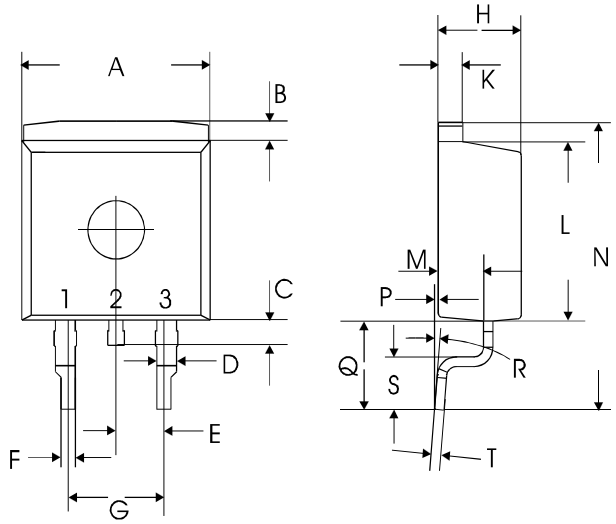


P-TO220-3-1

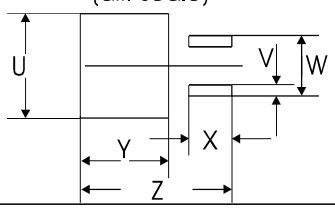


symbol	dimensions			
	[mm]		[inch]	
	min	max	min	max
A	9.70	10.30	0.3819	0.4055
B	14.88	15.95	0.5858	0.6280
C	0.65	0.86	0.0256	0.0339
D	3.55	3.89	0.1398	0.1531
E	2.60	3.00	0.1024	0.1181
F	6.00	6.80	0.2362	0.2677
G	13.00	14.00	0.5118	0.5512
H	4.35	4.75	0.1713	0.1870
K	0.38	0.65	0.0150	0.0256
L	0.95	1.32	0.0374	0.0520
M	2.54 typ.		0.1 typ.	
N	4.30	4.50	0.1693	0.1772
P	1.17	1.40	0.0461	0.0551
T	2.30	2.72	0.0906	0.1071

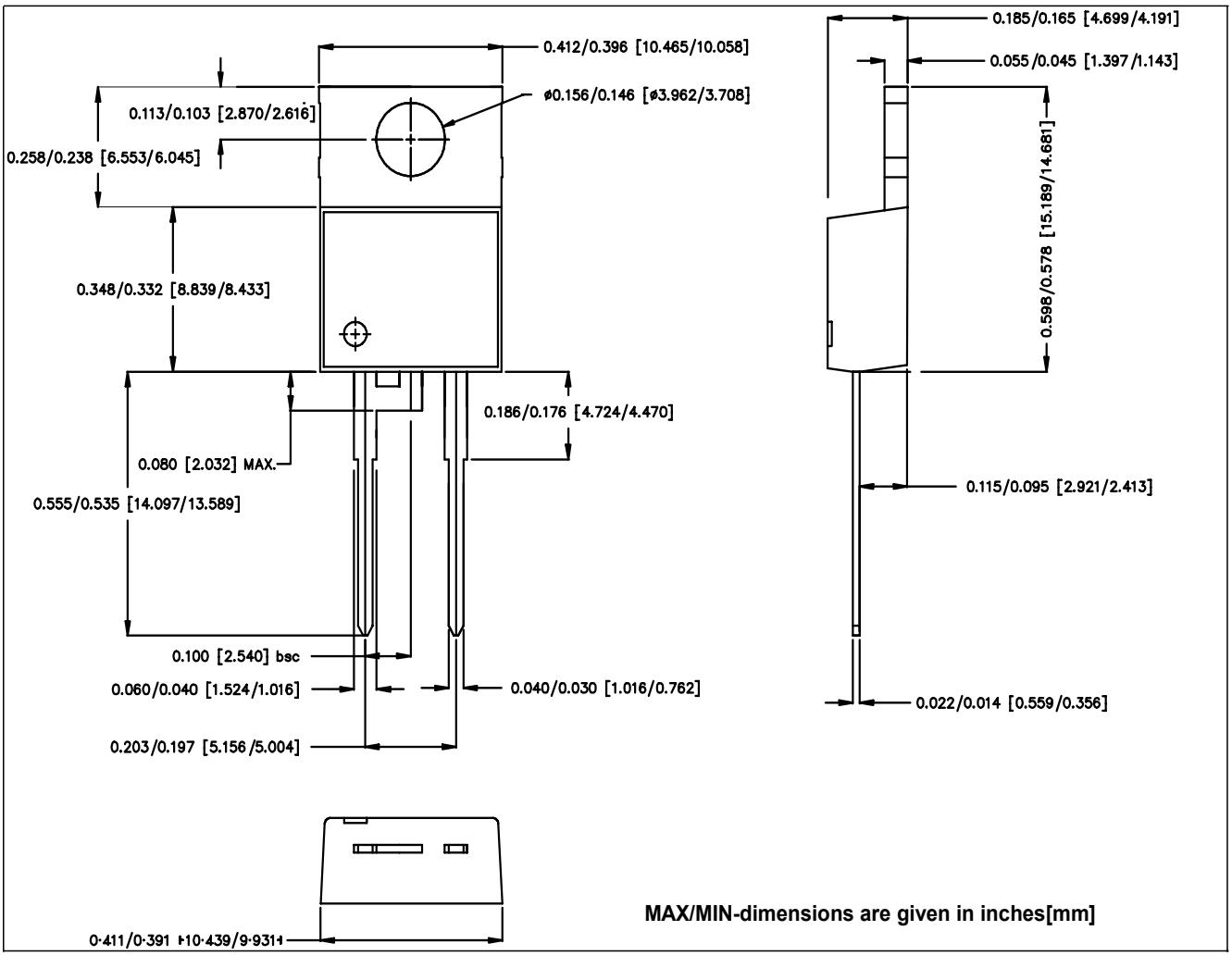
TO-220-3-45 (P-TO220SMD)



Footprint
(dif. scale)



symbol	dimensions			
	[mm]		[inch]	
	min	max	min	max
A	9.80	10.00	0.3858	0.3937
B	1.3 typ.		0.0512 typ.	
C	1.25	1.75	0.0492	0.0689
D	0.95	1.15	0.0374	0.0453
E	2.54 typ.		0.1 typ.	
F	0.72	0.85	0.0283	0.0335
G	5.08 typ.		0.2 typ.	
H	4.30	4.50	0.1693	0.1772
K	1.28	1.40	0.0504	0.0551
L	9.00	9.40	0.3543	0.3701
M	2.30	2.50	0.0906	0.0984
N	14.1 typ.		0.5551 typ.	
P	0.00	0.20	0.0000	0.0079
Q	3.30	3.90	0.1299	0.1535
R	8° max		8° max	
S	1.70	2.50	0.0669	0.0984
T	0.50	0.65	0.0197	0.0256
U	10.8 typ.		0.4252 typ.	
V	1.35 typ.		0.0532 typ.	
W	6.43 typ.		0.2532 typ.	
X	4.60 typ.		0.1811 typ.	
Y	9.40 typ.		0.3701 typ.	
Z	16.15 typ.		0.6358 typ.	


0.412/0.396 [10.465/10.058]
ø0.156/0.146 [ø3.962/3.708]
0.113/0.103 [2.870/2.616]
0.258/0.238 [6.553/6.045]
0.348/0.332 [8.839/8.433]
0.186/0.176 [4.724/4.470]
0.080 [2.032] MAX.
0.555/0.535 [14.097/13.589]
0.100 [2.540] bsc
0.060/0.040 [1.524/1.016]
0.040/0.030 [1.016/0.762]
0.203/0.197 [5.156/5.004]
0.411/0.391 [10.439/9.931]
0.185/0.165 [4.699/4.191]
0.055/0.045 [1.397/1.143]
0.598/0.578 [15.189/14.681]
0.115/0.095 [2.921/2.413]
0.022/0.014 [0.559/0.356]
MAX/MIN-dimensions are given in inches[mm]

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